AMENDMENTS TO THE CLAIMS

1. (Currently amended) A method of forming a semiconductor structure, comprising:

forming an isolation region in a semiconductor substrate; wherein

a first oxide layer is ~~on~~ supported by said substrate,

a first sacrificial layer is ~~on~~ supported by said first oxide layer, wherein said first sacrificial layer comprises an oxide, and

a first nitride layer is ~~on~~ supported by said first sacrificial layer.

2. (Original) The method of claim 1, wherein a second sacrificial layer is between said first sacrificial layer and said first oxide layer.

3. (Original) The method of claim 2, wherein said first sacrificial layer comprises silicon oxide, said second sacrificial layer comprises silicon nitride, said isolation region comprises an oxide, and said substrate comprises silicon.

4. (Original) The method of claim 3, further comprising:

removing said first nitride layer;

removing said first sacrificial layer; and

removing said second sacrificial layer.

5. (Original) The method of claim 3, wherein said first and second sacrificial layers each have a thickness less than the thickness of said first nitride layer.

6. (Original) The method of claim 5, wherein

said first sacrificial layer has a thickness of 10 to 250 Å; and

said second sacrificial layer has a thickness of 10 to 500 Å.

7. (Original) The method of claim 3, wherein said forming an isolation region comprises:

etching a trench into said substrate; and

filing said trench with said oxide.

8. (Currently amended) The method of claim 7, further comprising, prior to said forming said isolation region:

forming said first oxide layer ~~on~~ supported by said substrate by thermal oxidation;

forming said second sacrificial layer ~~on~~ supported by said first oxide layer by CVD;

forming said first sacrificial layer ~~on~~ supported by said second sacrificial layer by CVD; and

forming said first nitride layer ~~on~~ supported by said first sacrificial layer by CVD.

9. (Original) The method of claim 4, further comprising implanting ions in said substrate through said first oxide layer.

10. (Original) A method of forming a semiconductor device, comprising:

forming a semiconductor structure by the method of claim 9; and

forming a semiconductor device from said semiconductor structure.

11. (Original) A method of forming an electronic device, comprising:

forming a semiconductor device by the method of claim 10; and

forming an electronic device, comprising said semiconductor device.

12. (Currently amended) A method of forming a semiconductor structure, comprising:

removing a first nitride layer and a first sacrificial layer, wherein said first sacrificial layer comprises an oxide;

wherein a first oxide layer is ~~on~~ supported by a substrate,

said first sacrificial layer is ~~on~~ supported by said first oxide layer, and

said first nitride layer is ~~on~~ supported by said first sacrificial layer.

13. (Original) The method of claim 12, wherein a second sacrificial layer is between said first sacrificial layer and said first oxide layer.

14. (Original) The method of claim 13, further comprising removing said second sacrificial layer, and

wherein said first sacrificial layer comprises silicon oxide, said second sacrificial layer comprises silicon nitride, said isolation region comprises an oxide, and said substrate comprises silicon.

15. (Original) The method of claim 14, wherein said first and second sacrificial layers each have a thickness less than the thickness of said first nitride layer.

16. (Original) The method of claim 15, wherein

said first sacrificial layer has a thickness of 10 to 250 Å; and

said second sacrificial layer has a thickness of 10 to 500 Å.

17. (Original) The method of claim 14, further comprising implanting ions in said substrate through said first oxide layer.

18. (Original) A method of forming a semiconductor device, comprising:

forming a semiconductor structure by the method of claim 17; and

forming a semiconductor device from said semiconductor structure.

19. (Original) A method of forming an electronic device, comprising:

forming a semiconductor device by the method of claim 18; and

forming an electronic device, comprising said semiconductor device.

20-22. (Cancelled)

23. (Previously presented) The method of claim 3, wherein said forming an isolation region comprises depositing an oxide onto said first nitride layer and into a trench adjacent to said first nitride layer, said first sacrificial layer, and said first oxide layer.

24. (Previously presented) The method of claim 1, wherein said first sacrificial layer is in contact with said first nitride layer.

25. (Currently amended) A method of forming a semiconductor structure, comprising:

forming an isolation region in a semiconductor substrate;

wherein a first oxide layer is ~~on~~ supported by said substrate,

a first nitride layer is ~~on~~ supported by said first oxide layer, and

a first sacrificial layer is between said first oxide layer and said first nitride layer.

26. (Previously presented) The method of claim 24, wherein a second sacrificial layer is between said first sacrificial layer and said first oxide layer.